24 February 2004

Updated Search

09/782,216

2, 100	·····	1 oppowien search		01/ +84,61
L Number	Hits	Search Text	DB	Time stamp
-	0	476526.apn.	USPAT;	2003/07/29
			US-PGPUB;	11:13
			EPO; JPO;	
			DERWENT	
_	1	6547937.pn.	USPAT;	2003/07/29
			US-PGPUB;	14:25
			EPO; JPO;	
			DERWENT	
-	152	204/\$.ccls. and (cleaning adj electrode)	USPAT;	2003/07/28
			US-PGPUB;	16:24
			EPO; JPO;	
			DERWENT	
-	17	(204/\$.ccls. and (cleaning adj electrode)) and	USPAT;	2003/07/28
		(microelectronic or wafer or semiconductor)	US-PGPUB;	16:24
		•	EPO; JPO;	
			DERWENT	
-	12396	204/\$.ccls. and (anode same cathode)	USPAT;	2003/07/29
		, ,	US-PGPUB;	10:53
			EPO; JPO;	
			DERWENT	
-	1	782216.apn.	USPAT;	2003/07/29
			US-PGPUB;	13:12
			EPO; JPO;	
			DERWENT	
_	59395	204/\$.ccls.	USPAT;	2003/07/29
	0,0,0	αο η φ ιοσίοι	US-PGPUB;	13:12
			EPO; JPO;	
			DERWENT	
_	35240	205/\$.ccls.	USPAT;	2003/07/29
	332.5		US-PGPUB;	13:13
			EPO; JPO;	
			DERWENT	
_	83968	204/\$.ccls. 205/\$.ccls.	USPAT;	2003/07/29
		αο 17 φ.οσίο. ασσ7 φ.οσίο.	US-PGPUB;	13:13
			EPO; JPO;	10.13
			DERWENT	
_	10782	(204/\$.ccls. 205/\$.ccls.) and (microelectronic or	USPAT;	2003/07/29
	10,01	semiconductor or wafer)	US-PGPUB;	13:13
		The state of the s	EPO; JPO;	-50
			DERWENT	
_	1310	((204/\$.ccls. 205/\$.ccls.) and (microelectronic or	USPAT;	2003/07/29
-		semiconductor or wafer)) and ((second or secondary	US-PGPUB;	13:14
		or another or additional) near (electrode or cathode	EPO; JPO;	
		,	1	
_	574	• •		2003/07/29
	3,4	The state of the s	1	
		•		13.10
		asposity hear a failude of carmode of electrode))	i i	
-	574	or anode)) ((204/\$.ccls. 205/\$.ccls.) and (microelectronic or semiconductor or wafer)) and ((clean\$5 or strip\$5 deposit) near2 (anode or cathode or electrode))	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:18

·				· · · · · · · · · · · · · · · · · · ·
-	174	(((204/\$.ccls. 205/\$.ccls.) and (microelectronic or	USPAT;	2003/07/29
		semiconductor or wafer)) and ((second or secondary	US-PGPUB;	13:18
		or another or additional) near (electrode or cathode	EPO; JPO;	
		or anode))) and (((204/\$.ccls. 205/\$.ccls.) and	DERWENT	
		(microelectronic or semiconductor or wafer)) and		
		((clean\$5 or strip\$5 deposit) near2 (anode or		
		cathode or electrode)))		
1	93	((((204/\$.ccls. 205/\$.ccls.) and (microelectronic or	USPAT;	2003/07/29
_	23			13:18
		semiconductor or wafer)) and ((second or secondary	US-PGPUB;	13.10
		or another or additional) near (electrode or cathode	EPO; JPO;	
		or anode))) and (((204/\$.ccls. 205/\$.ccls.) and	DERWENT	
		(microelectronic or semiconductor or wafer)) and]	
		((clean\$5 or strip\$5 deposit) near2 (anode or		
		cathode or electrode)))) and (etch\$5)		
-	462	205/640,646,648,652,686.ccls.	USPAT;	2003/07/29
			U5-PGPUB;	14:26
			EPO; JPO;	
		·	DERWENT	
	98	205/640,646,648,652,686.ccls. and clean\$5	USPAT;	2003/07/29
-	70	200/040,040,040,002,000.ccis. and cleanipo	•	1
			US-PGPUB;	15:10
	1		EPO; JPO;	
			DERWENT	
	744	204/224m.ccls.	USPAT;	2003/07/29
			US-PGPUB;	15:10
			EPO; JPO;	
		· ·	DERWENT	
_	2427	204/275.1,237,242,280.ccls.	USPAT;	2003/07/30
			U5-PGPUB;	15:02
			EPO; JPO;	-0.02
			DERWENT	
	3092	204/224m.ccls. 204/275.1,237,242,280.ccls.	USPAT;	2003/07/29
	3072	104/124111.0013. 104/12/3.1,23/,242,200.0013.	US-PGPUB;	15:10
			1	15.10
			EPO; JPO;	
		(004/004 004/077400745555	DERWENT	
-	167	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and	USPAT;	2003/07/29
		((electrochem\$7 or electrol\$7 or (electro adj	U5-PGPUB;	15:12
		chem\$7)) near2 (etch\$5 or polish\$3))	EPO; JPO;	
			DERWENT	
-	100	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and	USPAT;	2003/07/29
		(electropolish\$5)	US-PGPUB;	15:12
		·	EPO; JPO;	
			DERWENT	
_	57	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and	USPAT;	2004/02/24
]	((electropolish\$5) with (electrode or anode or	US-PGPUB;	14:28
		cathode))	EPO; JPO;	17.60
		- carnode))	DERWENT	
	07	(204/224m and 204/275 1 227 242 280 la \ l		2002/07/20
-	87	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and	USPAT;	2003/07/29
		(((electrochem\$7 or electrol\$7 or (electro adj	US-PGPUB;	15:21
		chem\$7)) near2 (etch\$5 or polish\$3)) with	EPO; JPO;	
		(electrode or cathode or anode))	DERWENT	
-	809	(204/\$.ccls. 205/\$.ccls.) and ((((builld or built) adj	USPAT;	2003/08/01
		up) or deposit\$5 or collect\$3) with (electrode or	US-PGPUB;	09:03
		cathode or electrode) with (distance or gap or	EPO; JPO;	
		spacing))	DERWENT	

	T		I	
-	179	(204/\$.ccls. 205/\$.ccls.) and (((((builld or built) adj	USPAT;	2003/07/29
		up) or deposit\$5 or collect\$3) with (electrode or	US-PGPUB;	15:25
		cathode or electrode) with (distance or gap or	EPO; JPO;	
		spacing)) same (remov\$4 or clean\$3 or strip\$4 or etch\$4))	DERWENT	
_	804	(204/\$.ccls. 205/\$.ccls.) and (((((builld or built) adj	USPAT;	2003/07/29
		up) or deposit\$5 or collect\$3) with (electrode or	US-PGPUB;	15:28
		cathode or electrode) with (distance or gap or	EPO; JPO;	
		spacing)) same ((remov\$4 or clean\$3 or strip\$4 or	DERWENT	
		etch\$4) with ((builld or built) adj up) or deposit\$5 or		
İ		collect\$3))		
_	133	(204/\$.ccls. 205/\$.ccls.) and (((((builld or built) adj	USPAT;	2003/07/29
		up) or deposit\$5 or collect\$3) with (electrode or	US-PGPUB;	15:29
	ļ	cathode or electrode) with (distance or gap or	EPO; JPO;	
		spacing)) same ((remov\$4 or clean\$3 or strip\$4 or	DERWENT	
		etch\$4) with (((builld or built) adj up) or deposit\$5		
		or collect\$3)))		
-	3	(("6500324") or ("6174425")).PN.	USPAT;	2003/07/30
			US-PGPUB;	09:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	8867	204/\$.ccls. and (microelectronic or semiconductor or	USPAT;	2003/07/30
		wafer)	US-PGPUB;	10:30
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2347	(204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
		or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	10:31
	S.	(fluid or solution or electrolyte))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1056	(204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
		or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	13:15
		(fluid or solution or electrolyte) with (conduit or path	EPO; JPO;	
		or pathway or port or passage or passageway or flow	DERWENT;	
		or opening or inlet or outlet))	IBW_TDB	
-	65	((204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
		or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	13:17
		(fluid or solution or electrolyte) with (conduit or path	EPO; JPO;	
		or pathway or port or passage or passageway or flow	DERWENT;	
	75	or opening or inlet or outlet))) and (mesh with anode)	IBM_TDB	2003/07/20
_	75	((204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30 14:14
		or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path	US-PGPUB; EPO; JPO;	14.14
		or pathway or port or passage or passageway or flow	DERWENT;	
		or parnway or port or passage or passageway or now or opening or inlet or outlet))) and (mesh with (anode	IBM_TDB	
		or porous))	1011_100	
_	160	((204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
		or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	14:15
		(fluid or solution or electrolyte) with (conduit or path	EPO; JPO;	
		or pathway or port or passage or passageway or flow	DERWENT;	
		or opening or inlet or outlet))) and (anode with (mesh	IBM_TDB	
		or porous))		
L			·	·

110 ((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode with rotat\$5) 125 ((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7)) (((204/\$.ccls. and (microelectronic or semiconductor or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7)) (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and ((204/\$.ccls. and (microelectronic or semiconductor or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and ((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and ((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and ((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and ((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or opening or inlet or outlet)))
(fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode with rotat\$5) 125 ((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7)) 60 (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer))) and ((anode or cathode or electrode) with (fluid or	
or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode with rotat\$5) ((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7)) (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (conduit or path or pathway or port or passage or passageway or flow or pathway or port or passage or passageway or flow or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer))) and ((anode or cathode or electrode) with (fluid or	
or opening or inlet or outlet))) and (anode with rotat\$5) 125 ((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7)) 60 (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or pathway or port or passage or passageway or flow or pathway or port or passage or passageway or flow or pathway or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or	
rotat\$5) 125 ((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7)) 60 (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or pathway or port or passage or passageway or flow (rotat\$5 or mov\$7))) and (anode near2 (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or	
or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7)) (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or pathway or port or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or	
(fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7)) (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or pathor or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or)
or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7)) (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or)
or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7)) 60 (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or)
(rotat\$5 or mov\$7)) (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or pathway or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or)
- (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (5.23 (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or)
or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or	
(fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or	
or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 IBM_TDB (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or	I
or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or	1
(rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or	
(microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or	
((anode or cathode or electrode) with (fluid or	
pathway or port or passage or passageway or flow or	
opening or inlet or outlet))) and (anode with (mesh or	
porous)))	
- 2 6197182.pn. USPAT; 2003/07/3	'
US-PGPUB; 14:35	
EPO; JPO;	
DERWENT;	Ì
IBM_TDB	
- 1349 204/\$.ccls. and (solution with ((rins\$4 or clean\$5) USPAT; 2003/07/3	'
and (electroplat\$5 or electroly\$6 or plating))) US-PGPUB; 14:39	
EPO; JPO;	
DERWENT;	
IBM_TDB	
- 765 (204/\$.ccls. and (solution with ((rins\$4 or clean\$5) USPAT; 2003/07/3	'
and (electroplat\$5 or electroly\$6 or plating)))) not US-PGPUB; 14:40	
rinsed! EPO; JPO;	
DERWENT;	
IBM_TDB	
- 3 ((("6103096") or ("5614076") or ("5531874") or USPAT; 2003/07/3)
("5486282") or ("5543032") or ("5536388") or US-PGPUB; 14:43	
("5567300") or ("5284554")).PN.) and ((rins\$ or EPO; JPO;	1
clean\$) with (plating or electroly\$5 or DERWENT;	
electroplat\$5)) IBM_TDB	
- 5 6103096.URPN. USPAT 2003/07/3)
14:44	
- 15 (("6103096") or ("5614076") or ("5531874") or USPAT; 2003/07/3	
("5486282") or ("5543032") or ("5536388") or US-PGPUB; 14:49	,
("5567300") or ("5284554")).PN. EPO; JPO;)
DERWENT;)
IBM_TDB)
- 29 5567300.URPN. USPAT 2003/07/3)
14:47	

-	20	5543032.URPN.	USPAT	2003/07/30
				14:48
-	6	5536388.URPN.	USPAT	2003/07/30
				14:48
_	15	5486282.URPN.	U5PAT	2003/07/30
				14:48
_	19	5284554.URPN.	USPAT	2003/07/30
				14:48
_	62	5567300.URPN. 5543032.URPN. 5536388.URPN.	USPAT;	2003/07/30
		5486282.URPN. 5284554.URPN.	US-PGPUB;	14:49
	ļ		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	0	(5567300.URPN. 5543032.URPN. 5536388.URPN.	USPAT;	2003/07/30
		5486282.URPN. 5284554.URPN.) and (clean\$5 with	US-PGPUB;	14:50
		(electrode or cathode or anode))	EPO; JPO;	14.50
		(electrode or carnode or anode))	DERWENT;	
			1	
	24	/EE/7200 IDDA EE/2022 IDDA EE2/200 IDDA	IBM_TDB	2002/07/20
-	26	(5567300.URPN. 5543032.URPN. 5536388.URPN.	USPAT;	2003/07/30
		5486282.URPN. 5284554.URPN.) and (remov\$5 with	US-PGPUB;	14:55
		(electrode or cathode or anode))	EPO; JPO;	
			DERWENT;	
			IBW_TDB	
-	83968	204/\$.ccls. 205/\$.ccls.	USPAT;	2003/07/30
ļ.			US-PGPUB;	14:56
			EPO; JPO;	
			DERWENT;	
	1	,	IBW_TDB	
-	3	(204/\$.ccls. 205/\$.ccls.) and (electrochem\$7 near	USPAT;	2004/02/24
		(micromachin\$5 or machin\$5)) and (clean\$ near	US-PGPUB;	14:32
		(electrode or cathode or anode))	EPO; JPO;	
			DERWENT;	
	}		IBW_TDB	
-	295	204/275.1,237,242,280.ccls. and (titanium with	USPAT;	2003/07/30
		(platinum or platinized))	US-PGPUB;	15:05
			EPO; JPO;	
1			DERWENT	
-	83	(204/275.1,237,242,280.ccls. and (titanium with	USPAT;	2003/07/30
		(platinum or platinized))) and (microelectronic or	US-PGPUB;	15:06
		semiconductor or wafer)	EPO; JPO;	
			DERWENT	
_	18	(("5312532") or ("5344491") or ("5421987") or	USPAT;	2003/07/31
	•	("5431421") or ("5516412") or ("5925226") or	US-PGPUB;	11:08
		("6001235") or ("6228231") or ("6251250")).PN.	EPO; JPO;	
]	, , , , , , , , , , , , , , , , , , , ,	DERWENT;	
			IBM_TDB	
	8	ep-0343502-\$.did. ep-0726698-\$.did.	USPAT;	2003/07/31 11:11
		jp-62297494-\$.did. jp-62297495-\$-did.	US-PGPUB;	
		jp-1120827-\$.did. jp-5175158-\$.did.	EPO; JPO;	
		jp-6260468-\$.did. jp-7211724-\$.did.	DERWENT;	
		jp-7284738-\$.did. jp-10172974-\$.did.	IBM_TDB	
		jp-11092993-\$.did. jp-2000017480-\$.did.	10.4 100	
L	<u> </u>	JP **********#.did. JP************************************	J	1

-	840	(204/\$.ccls. 205/\$.ccls.) and ((((build or built) adj	USPAT;	2003/08/01
		up) or deposit\$5 or collect\$3) with (electrode or	US-PGPUB;	09:04
		cathode or electrode) with (distance or gap or	EPO; JPO;	
		spacing))	DERWENT	
-	2	6328872.pn.	USPAT;	2004/02/24
		·	US-PGPUB;	13:32
		~~	EPO; JPO;	
			DERWENT	
_	22	("3395092" "3436259" "3890746" "3959089"	USPAT	2004/02/24
		"4153523" "4395320" "4610772" "4919769"		13:36
		"5024735" "5171412" "5429733" "5558568"		
		"5650039" "5692947" "5755859" "5807165"		
		"5833820" "5863412" "5930669" "5933753"		
		"6004880" "6017820").PN.		
_	19	("2751340" "2859166" "3880725" "4148707"	USPAT	2004/02/24
		"4304641" "4420382" "4421627" "4466864"	051711	14:02
		"4678545" "4720329" "4879007" "5084153"		14.02
		"5135636" "5149419" "5230743" "5312532"		
		"5332487" "5582708" "5620581").PN.		
	7	6174425.URPN.	USPAT	2004/02/24
	/	6174425.URPIN.	USPAT	2004/02/24
	2/0	204/202	LICOAT	14:06
-	360	204/222.ccls.	USPAT;	2004/02/24
			US-PGPUB;	14:12
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	817	204/224r.ccls.	USPAT;	2004/02/24
			US-PGPUB;	14:12
			EPO; JPO;	
			DERWENT;	
			IBW_TDB	
-	1158	204/222.ccls. 204/224r.ccls.	USPAT;	2004/02/24
			US-PGPUB;	14:13
			EPO; JPO;	
•			DERWENT;	
			IBW_TDB	
-	13	(204/222.ccls. 204/224r.ccls.) and (clean\$3 near	USPAT;	2004/02/24
		(electrode or anode or cathode))	US-PGPUB;	14:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	23	(204/222.ccls. 204/224r.ccls.) and	USPAT;	2004/02/24
		((electropolish\$5) with (electrode or anode or	US-PGPUB;	14:28
		cathode))	EPO; JPO;	
		"	DERWENT	
-	О	(204/222.ccls. 204/224r.ccls.) and (electrochem\$7	USPAT;	2004/02/24
		near (micromachin\$5 or machin\$5)) and (clean\$ near	US-PGPUB;	14:32
		(electrode or cathode or anode))	EPO; JPO;	-
			DERWENT;	
			IBM_TDB	*
L	L	<u> </u>		l